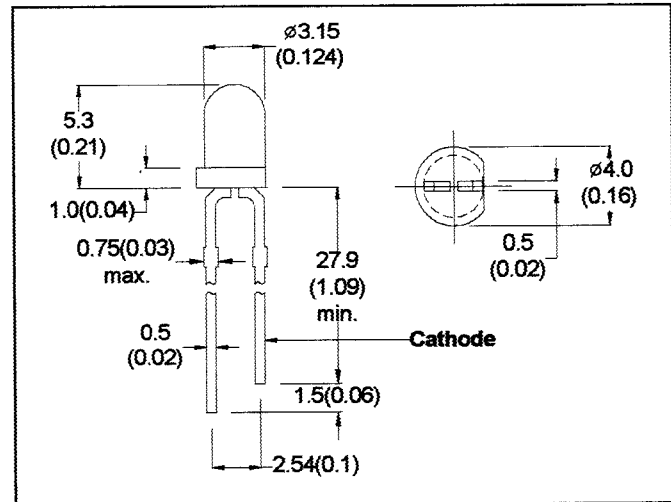


# MICRO ELECTRONICS

## INFRARED EMITTING DIODE

### DESCRIPTION

MIB31TA-2 is GaAlAs infrared emitting diode molded in T-1 standard 3mm diameter clear transparent lens.



- All Dimension in mm (inch)
- NO Scale
- Tol : +/- 0.3mm

### ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Forward Current (Continuous)	100mA
Pulse Forward Current	1A*
Reverse Voltage (Continuous)	5V
Power Dissipation	200mW
Operating Temperature Range	-25 to +85°C
Lead Soldering Temperature (1/16" from body)	260°C for 5 sec.

\* Pulse Width = 10μs, Duty Ratio = 0.01.

### ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS
Radiant Power Output	P <sub>o</sub>	2.2	3.5		mW	I <sub>F</sub> =20mA
Forward Voltage	V <sub>F</sub>		1.7	2.0	V	I <sub>F</sub> =20mA
Reverse Current	I <sub>R</sub>			100	μA	V <sub>R</sub> =5V
Peak Wavelength	λ <sub>p</sub>		770		nm	I <sub>F</sub> =20mA
Spectrum Line Half Width	Δλ		30		nm	I <sub>F</sub> =20mA
Viewing Angle	2θ 1/2		40		degree	I <sub>F</sub> =20mA

MICRO ELECTRONICS LTD.

38, Hung To Road, Microtron Building, Kwun Tong, Kowloon, Hong Kong.  
Kwun Tong P.O. Box 69477 Hong Kong. Fax No. 2341 0321 Telex:43510 Micro Hx. Tel: 2343 0181-5

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